

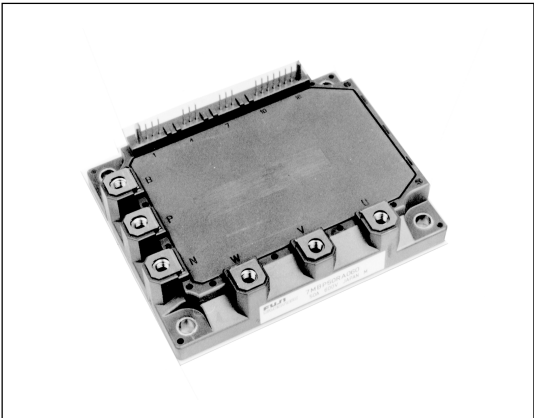
6MBP100RTB060

IPM-R3 series

600V / 100A 6 in one-package

Features

- Temperature protection provided by directly detecting the junction temperature of the IGBTs
- Low power loss and soft switching
- High performance and high reliability IGBT with overheating protection
- Higher reliability because of a big decrease in number of parts in built-in control circuit



Maximum ratings and characteristics

● Absolute maximum ratings(at Tc=25°C unless otherwise specified)

Item			Symbol	Rating		Unit
				Min.	Max.	
DC bus voltage			V _{DC}	0	450	V
DC bus voltage (surge)			V _{DC(surge)}	0	500	V
DC bus voltage (short operating)			V _{SC}	200	400	V
Collector-Emitter voltage			V _{CES} *1	0	600	V
INV	Collector current	DC	I _C	-	100	A
		1ms	I _{CP}	-	200	A
		Duty=72.3%	-I _C *2	-	100	A
	Collector power dissipation	One transistor	P _C *3	-	347	W
Junction temperature			T _J	-	150	°C
Input voltage of power supply for Pre-Driver			V _{CC} *4	-0.5	20	V
Input signal voltage			V _{in} *5	-0.5	V _{CC} +0.5	V
Input signal current			I _{in}	-	3	mA
Alarm signal voltage			V _{ALM} *6	-0.5	V _{CC}	V
Alarm signal current			I _{ALM} *7	-	20	mA
Storage temperature			T _{stg}	-40	125	°C
Operating case temperature			T _{opr}	-20	100	°C
Isolating voltage (Case-Terminal)			V _{iso} *8	-	AC2.5	kV
Screw torque		Mounting (M5)		-	3.5 *9	N·m
		Terminal (M5)		-	3.5 *9	N·m

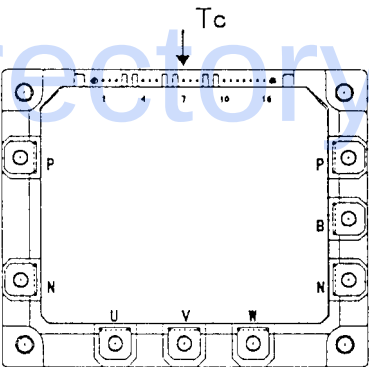


Fig.1 Measurement of case temperature

*1 : V_{CES} shall be applied to the input voltage between terminal P and U or V or W, N and U or V or W.
*2 : 125°C/FWD R_{th(j-c)}/(I_C x V_F MAX)=125/0.665/(100 x 2.6)x100=72.3%
*3 : P_C=125°C/IGBT R_{th(j-c)}=125/0.36=347W [Inverter]
*4 : V_{CC} shall be applied to the input voltage between terminal No. 3 and 1, 6 and 4, 9 and 7, 11 and 10.
*5 : V_{in} shall be applied to the input voltage between terminal No. 2 and 1, 5 and 4, 8 and 7, 13,14,15 and 10.
*6 : V_{ALM} shall be applied to the voltage between terminal No. 16 and 10.
*7 : I_{ALM} shall be applied to the input current to terminal No. 16.
*8 : 50Hz/60Hz sine wave 1 minute.
*9 : Recommendable Value : 2.5 to 3.0 N·m

● **Electrical characteristics** (at Tc=Tj=25°C, Vcc=15V unless otherwise specified.)

Main circuit

Item		Symbol	Condition		Min.	Typ.	Max.	Unit
INV	Collector current at off signal input	ICES	VCE=600V Vin terminal open.		-	-	1.0	mA
	Collector-Emitter saturation voltage	VCE(sat)	Ic=100A	Terminal	-	-	2.3	V
				Chip	-	1.8	-	
	Forward voltage of FWD	VF	-Ic=100A	Terminal	-	-	2.6	V
				Chip	-	1.6	-	
Turn-on time		ton	VDC=300V,Tj=125°C		1.2	-	-	μs
Turn-off time		toff	IC=100A Fig.1, Fig.6		-	-	3.6	
Reverse recovery time		trr	VDC=300V, IC=100A Fig.1, Fig.6		-	-	0.3	
Maximum Avalanche Energy (A non-repetition)		PAV	Internal wiring inductance=50nH Main circuit wiring inductace=54nH		100	-	-	mJ

● **Control circuit**

Item	Symbol	Condition	Min.	Typ.	Max.	Unit
Supply current of P-line side pre-driver(one unit)	Iccp	Switching Frequency : 0 to 15kHz Tc=-20 to 125°C Fig.7	-	-	18	mA
Supply current of N-line side pre-driver	ICCN		-	-	65	mA
Input signal threshold voltage (on/off)	Vin(th)	ON	1.00	1.35	1.70	V
		OFF	1.25	1.60	1.95	V
Input zener voltage	Vz	Rin=20k ohm	-	8.0	-	V
Alarm signal hold time	tALM	Tc=-20°C Fig.2	1.1	-	-	ms
		Tc=25°C Fig.2	-	2.0	-	ms
		Tc=125°C Fig.2	-	-	4.0	ms
Limiting resistor for alarm	RALM		1425	1500	1575	ohm

● **Protection Section** (Vcc=15V)

Item	Symbol	Condition	Min.	Typ.	Max.	Unit
Over Current Protection Level of Inverter circuit	Ioc	Tj=125°C	150		-	A
Over Current Protection Delay time	tDOC	Tj=125°C	-	5	-	μs
SC Protection Delay time	tSC	Tj=125°C Fig.4	-	-	8	μs
IGBT Chip Over Heating	TjOH	surface of IGBT chips	150		-	°C
Over Heating Protection Hysteresis	TjH	VDC=0V, Ic=0A, Case temperature	-	20	-	°C
Over Heating Protection Temperature Level	TcoH		110	-	125	°C
Over Heating Protection Hysteresis	TCH		-	20	-	
Under Voltage Protection Level	VUV		11.0	-	12.5	V
Under Voltage Protection Hysteresis	VH		0.2	0.5	-	

● **Thermal characteristics**(Tc=25°C)

Item			Symbol	Min.	Typ.	Max.	Unit
Junction to Case thermal resistance	INV	IGBT	Rth(j-c)	-	-	0.36	°C/W
		FWD	Rth(j-c)	-	-	0.665	°C/W
Case to fin thermal resistance with compound			Rth(c-f)	-	0.05	-	°C/W

● **Noise Immunity** (VDC=300V, Vcc=15V, Test Circuit Fig.5)

Item	Condition	Min.	Typ.	Max.	Unit
Common mode rectangular noise	Pulse width 1μs, polarity ±, 10minuets Judge : no over-current, no miss operating	±2.0	-	-	kV
Common mode lightning surge	Rise time 1.2μs, Fall time 50μs Interval 20s, 10 times Judge : no over-current, no miss operating	±5.0	-	-	kV

● **Recommendable value**

Item	Symbol	Min.	Typ.	Max.	Unit
DC Bus Voltage	VDC	-	-	400	V
Operating Supply Voltage of Pre-Driver	VCC	13.5	15.0	16.5	V
Screw torque (M5)	-	2.5	-	3.0	Nm

● **Weight**

Item	Symbol	Min.	Typ.	Max.	Unit
Weight	Wt	-	450	-	g

*9 : (For 1 device, Case is under the device)

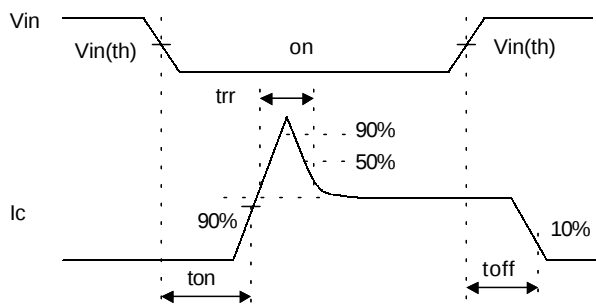
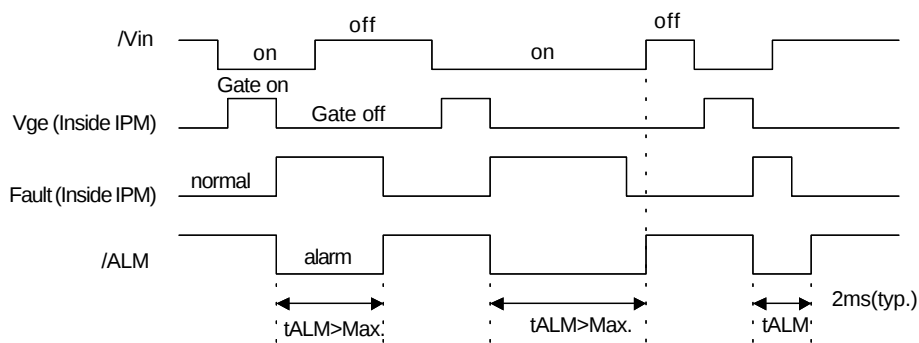


Figure 1. Switching Time Waveform Definitions



Fault : Over-current, Over-heat or Under-voltage

Figure 2. Input / Output Timing Diagram

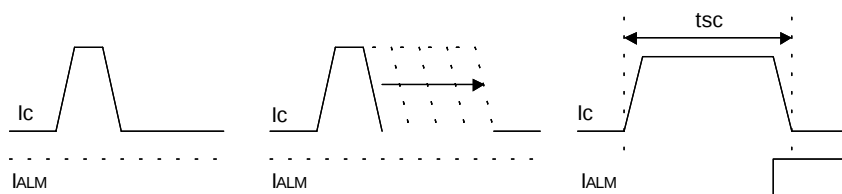


Figure. 4 Definition of tsc

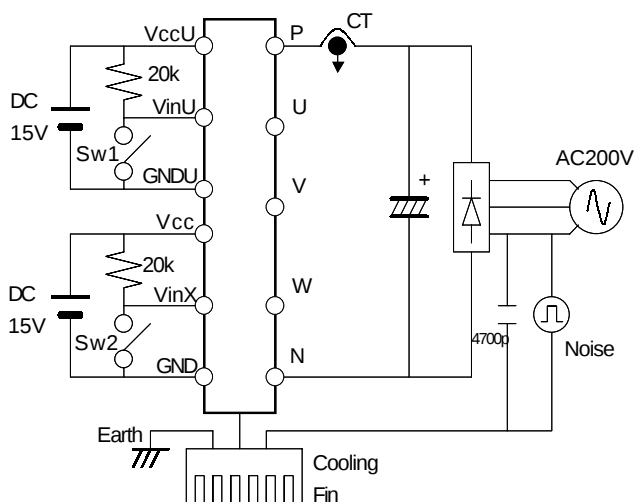


Figure 5. Noise Test Circuit

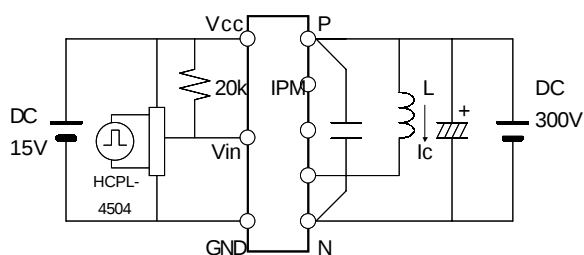


Figure 6. Switching Characteristics Test Circuit

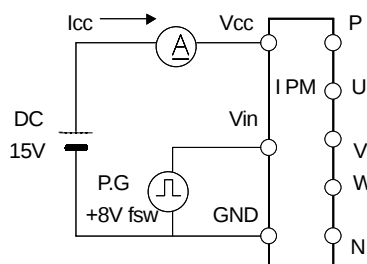
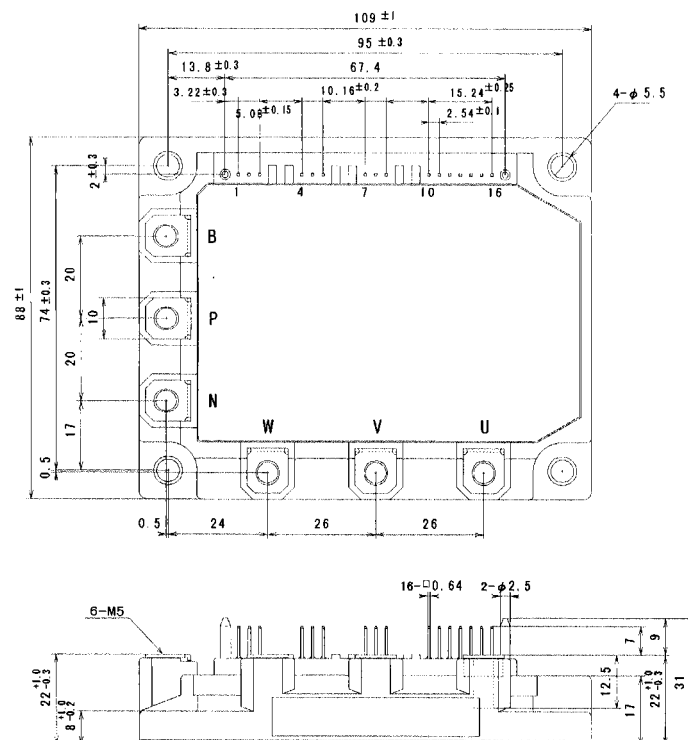
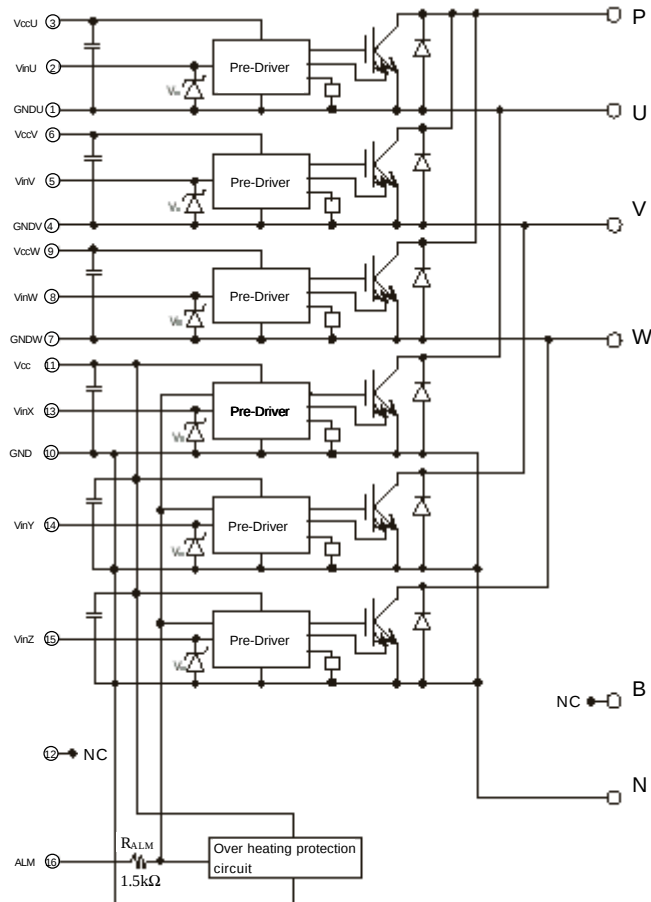
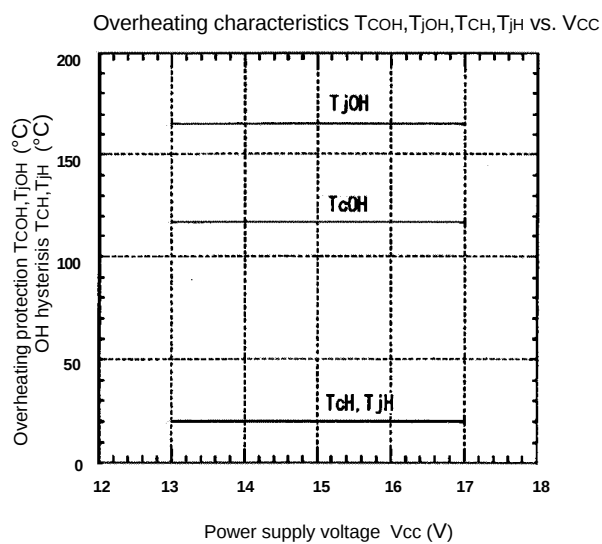
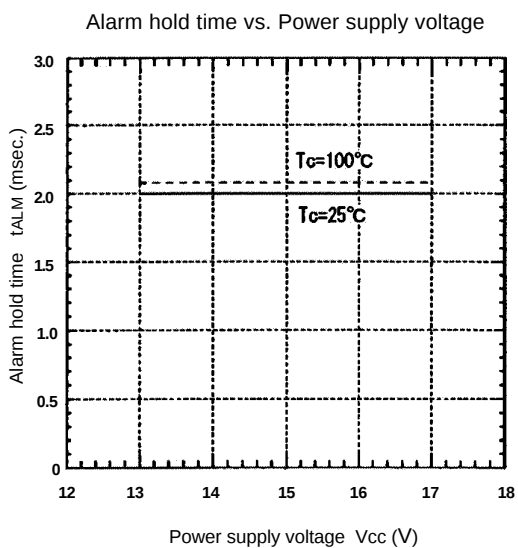
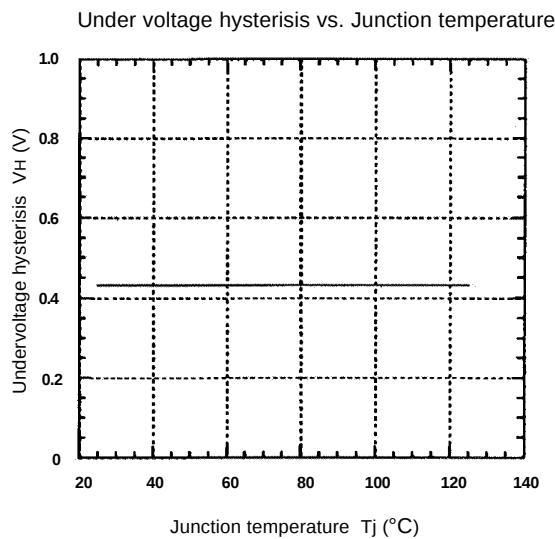
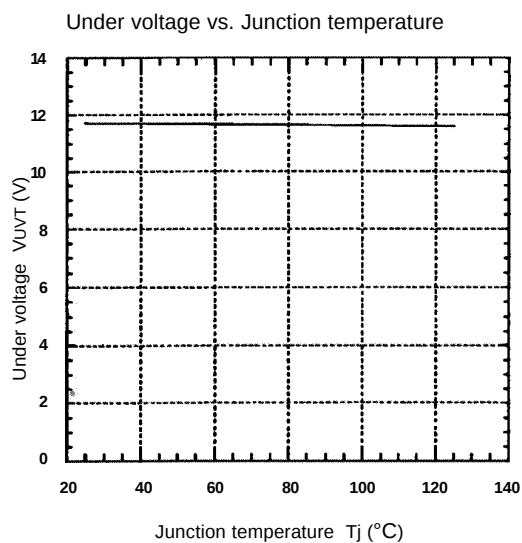
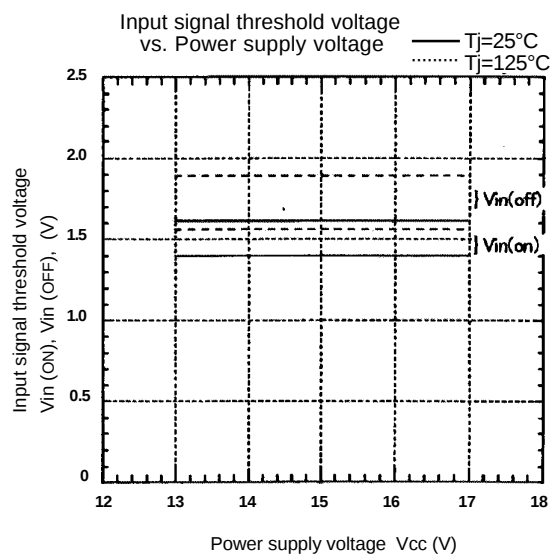
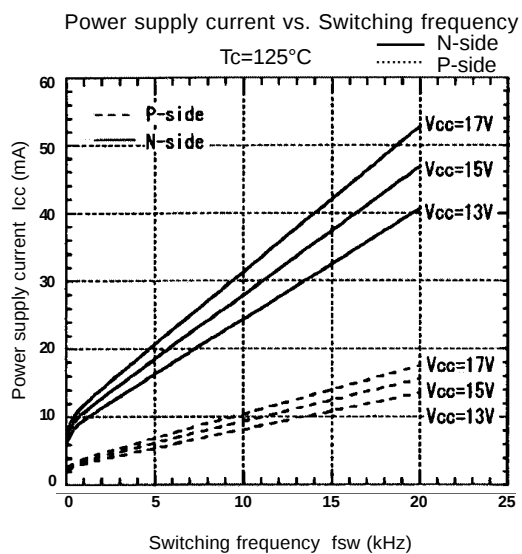


Figure 7. Icc Test Circuit



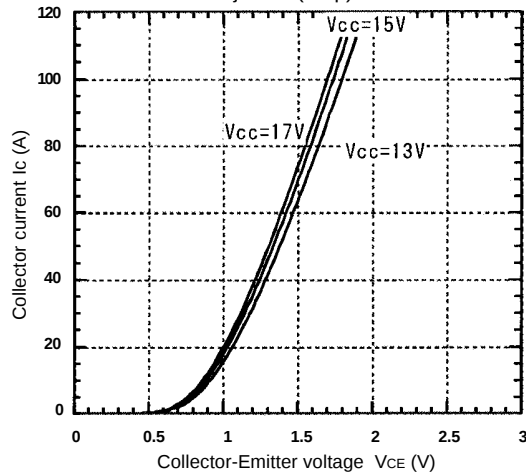
Characteristics

Control circuit characteristics (Representative)

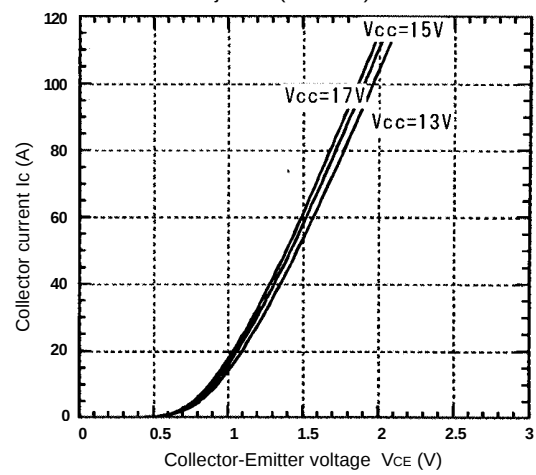


● Main circuit characteristics (Representative)

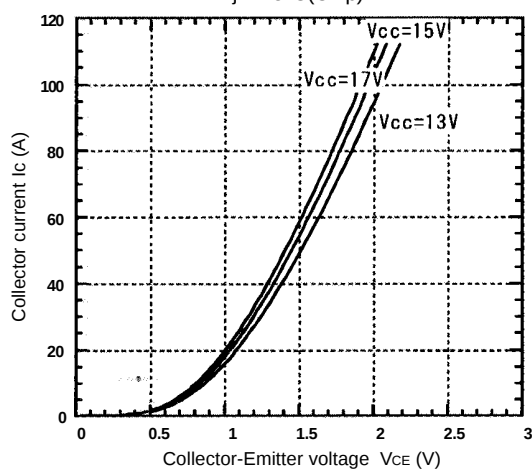
Collector current vs. Collector-Emitter voltage
T_j=25°C(Chip)



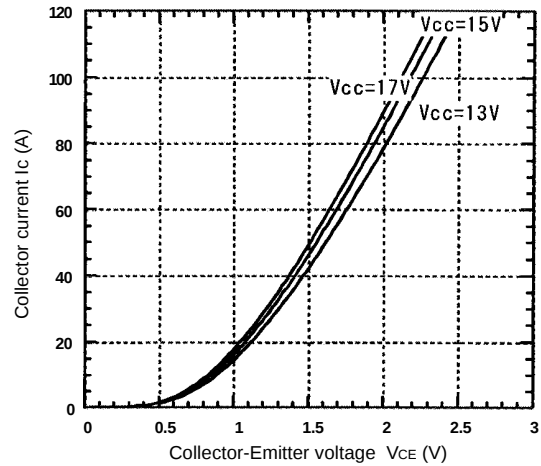
Collector current vs. Collector-Emitter voltage
T_j=25°C(Terminal)



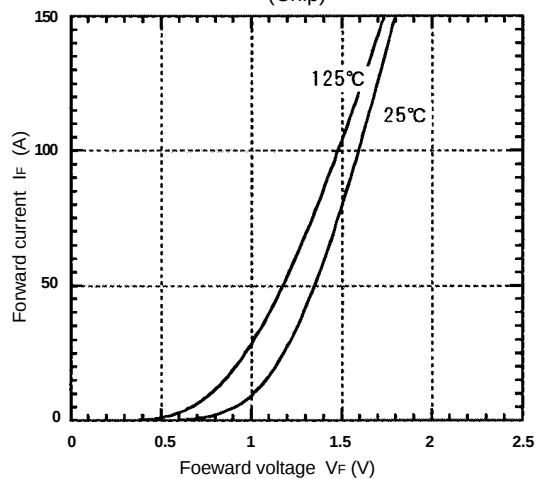
Collector current vs. Collector-Emitter voltage
T_j=125°C(Chip)



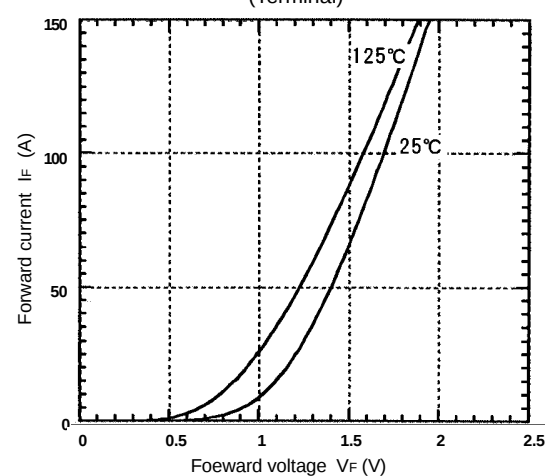
Collector current vs. Collector-Emitter voltage
T_j=125°C(Terminal)



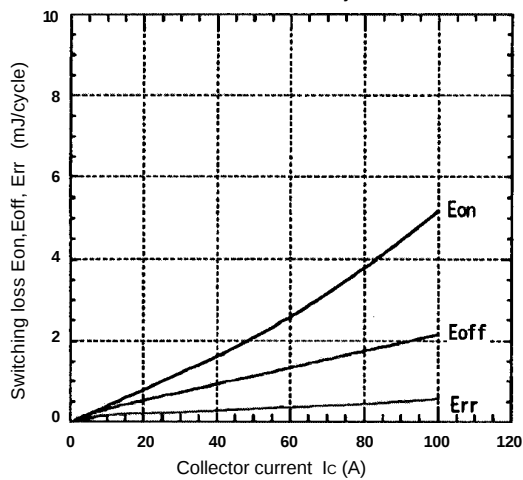
Forward current vs. Forward voltage
(Chip)



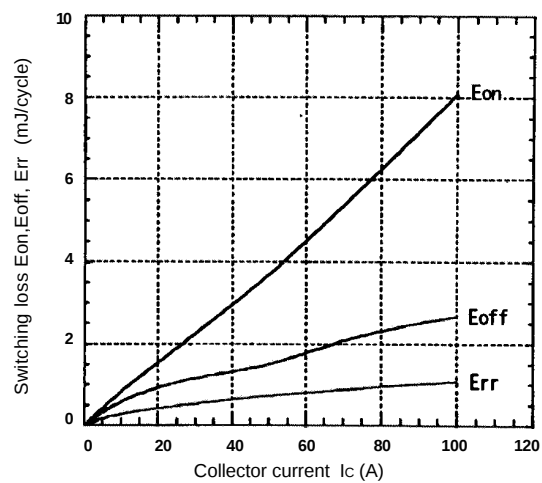
Forward current vs. Forward voltage
(Terminal)



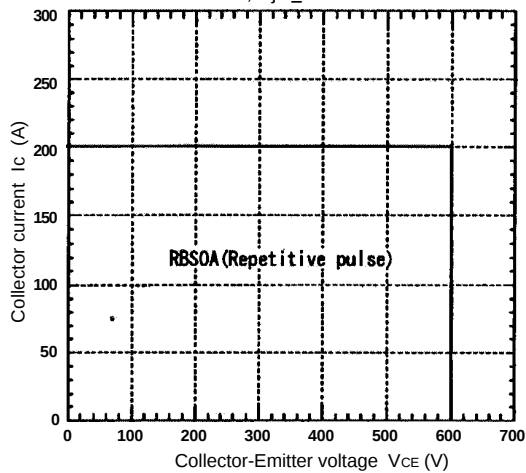
Switching Loss vs. Collector current
 $E_{dc}=300V$, $V_{cc}=15V$, $T_j=25^\circ C$



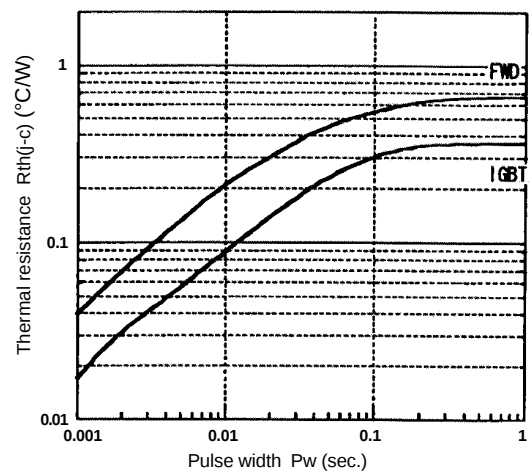
Switching Loss vs. Collector current
 $E_{dc}=300V$, $V_{cc}=15V$, $T_j=125^\circ C$



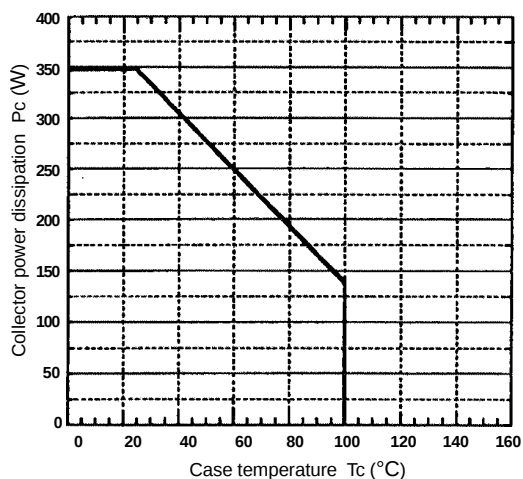
Reverse biased safe operating area
 $V_{cc}=15V$, $T_j \leq 125^\circ C$



Transient thermal resistance



Power derating for IGBT (per device)



Power derating for FWD (per device)

